

50 V, 3 A PNP low VCEsat (BISS) transistor Rev. 6 — 28 June 2011

Product data sheet

Product profile 1.

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350D

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High current capability
- High efficiency due to less heat generation

1.3 Applications

- Supply line switching circuits
- Battery management applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _C	collector current		-	-	-3	А
I _{CM}	peak collector current		-	-	-5	А
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	120	150	mΩ



- AEC-Q101 qualified
- Smaller Printed-Circuit Board (PCB) area than for conventional transistors
- DC-to-DC conversion

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	collector		
2	С	collector		1, 2, 5, 6
3	В	base	9	3
4	Е	emitter		4
5	С	collector	SOT457 (TSOP6)	4 sym030
6	С	collector		-,

3. Ordering information

Table 3. O	rdering information		
Type numbe	r Package		
	Name	Description	Version
PBSS5350D	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS5350D	53

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-3	А
I _{CM}	peak collector current			-	-5	А
I _{BM}	peak base current			-	-1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	600	mW
			[2]	-	750	mW
			[3]	-	1200	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for collector 1 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on an FR4 4-layer PCB.

6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	resistance in free air	<u>[1]</u>	-	-	208	K/W
	from junction to ambient		[2]	-	-	160	K/W
	απριστιί	pulsed; $t_p \le 50 \text{ ms}; \delta \le 0.5.;$ in free air	[2]	-	-	100	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

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7. Characteristics

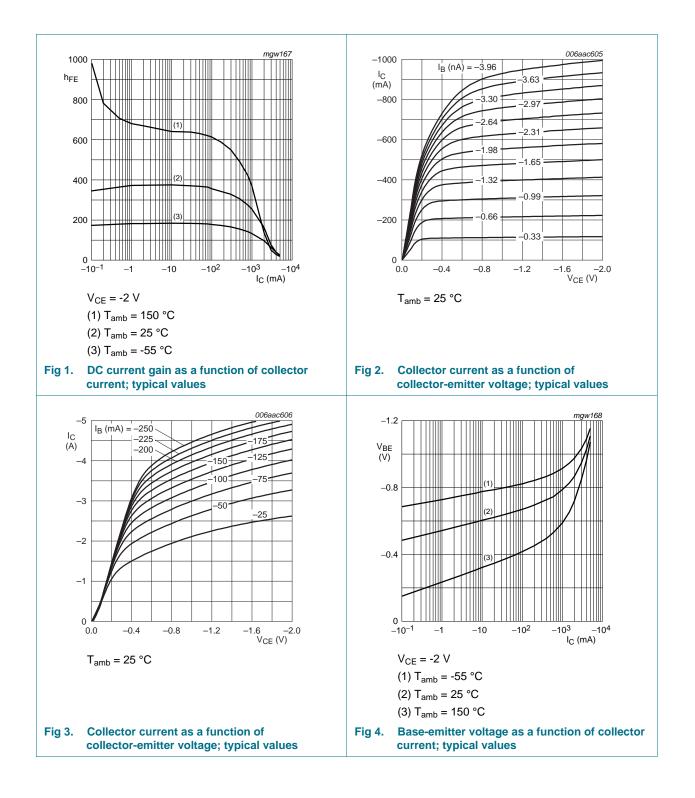
Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	V_{CB} = -50 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I _C = -500 mA; T _{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I _C = -1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I _C = -2 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; T_{amb} = 25 °C	-	-	-100	mV
		$I_{C} = -1 \text{ A}; I_{B} = -50 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-	-180	mV
		$I_C = -2 \text{ A}; I_B = -200 \text{ mA}; \text{ pulsed};$	-	-	-300	mV
R _{CEsat}	collector-emitter saturation resistance	$t_p ≤ 300 µs; δ ≤ 0.02; Tamb = 25 °C$	-	120	150	mΩ
V _{BEsat}	base-emitter saturation voltage		-	-	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I _C = -1 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-	-1.1	V
f _T	transition frequency	V_{CE} = -5 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	40	pF

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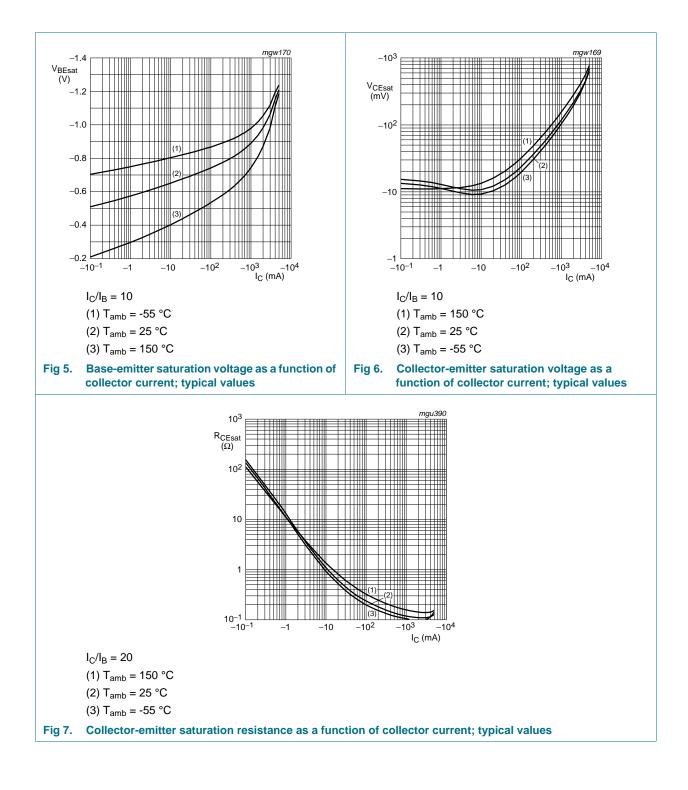


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8. Package outline

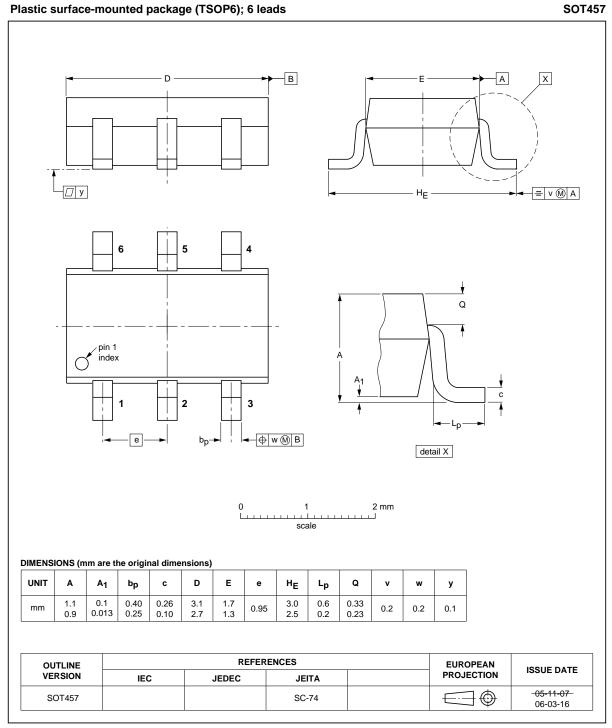
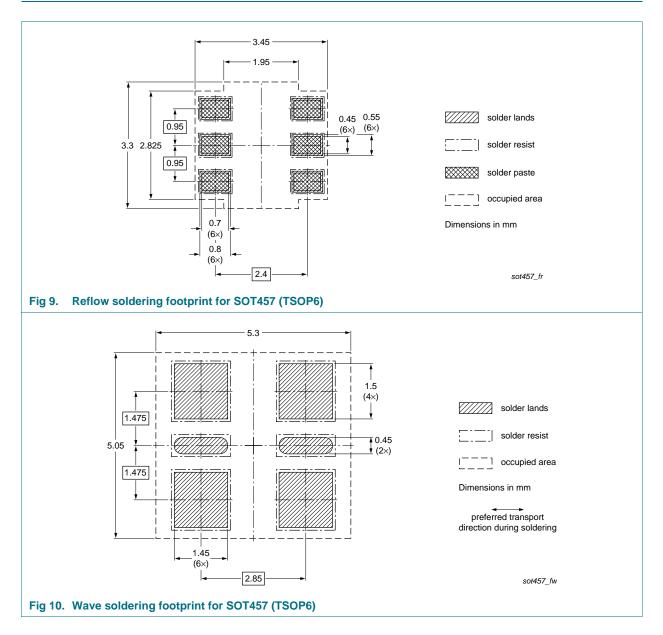


Fig 8. Package outline SOT457 (TSOP6)

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9. Soldering



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10. Revision history

Table 8. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5350D v.6	20110628	Product data sheet	-	PBSS5350D v.5
Modifications:	 <u>5</u> "Limiting va 	lues": P _{tot} conditions updated	d.	
PBSS5350D v.5	20110323	Product data sheet	-	PBSS5350D v.4
PBSS5350D v.4	20011113	Product specification	-	PBSS5350D v.3
PBSS5350D v.3	20010713	Product specification	-	PBSS5350D v.2
PBSS5350D v.2	20010126	Product specification	-	PBSS5350D v.1
PBSS5350D v.1	20000308	Product specification	-	-

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11. Legal information

11.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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